



DSS4240Y

40V LOW $V_{\text{CE(SAT)}}$ NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Complementary PNP Type Available (DSS5240Y)
- Ultra Small Surface Mount Package
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- ESD rating: 400V-MM, 8KV-HBM
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper Plated Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)





Top View



Top View Device Schematic



Top View Pin Out Configuration

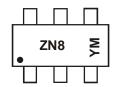
Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS4240Y-7	ZN8	7	8mm	3,000

Notes:

- 1. No purposefully added lead.
- 2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



ZN8 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

	Date Code Itey												
Ī	Year	20	10	20	11	2012 2013		2012 2013		2014		2015	
	Code	Code X		,	Υ		Z		4		3	С	
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	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Ī	Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V_{CBO}	40	V	
Collector-Emitter Voltage	V_{CEO}	40	V	
Emitter-Base Voltage	V_{EBO}	5	V	
Collector Current - Continuous	Ic	2	Α	
Peak Pulse Collector Current	I _{CM}	3	Α	
Peak Base Current	I _{BM}	0.3	Α	

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ T _A = 25°C	P _D	625	mW
Thermal Resistance, Junction to Ambient (Note 4) @ T _A = 25°C	$R_{ hetaJA}$	200	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

4. Device mounted on FR-4 PCB, with minimum recommended pad layout.

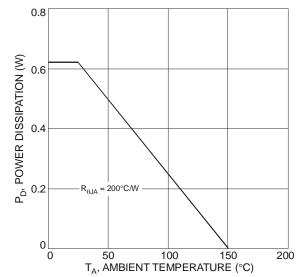
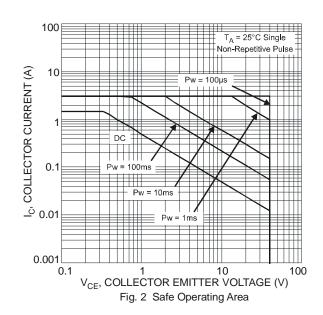


Fig. 1 Power Dissipation vs. Ambient Temperature (Note 3)



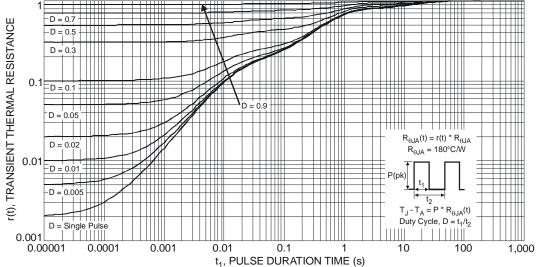


Fig. 3 Transient Thermal Response



Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	150	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 5)	BV _{CEO}	40	55	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	5	8.5	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_		100 50	nA μA	$V_{CB} = 30V, I_E = 0$ $V_{CB} = 30V, I_E = 0, T_A = 150^{\circ}C$
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	V _{EB} = 4V, I _C = 0
DC Current Gain (Note 5)	h _{FE}	350 300 300 150	_ _ _			$V_{CE} = 2V, I_C = 100 \text{mA}$ $V_{CE} = 2V, I_C = 500 \text{mA}$ $V_{CE} = 2V, I_C = 1A$ $V_{CE} = 2V, I_C = 2A$
Collector-Emitter Saturation Voltage (Note 5)	V _{CE(sat)}	_ _ _ _	45 52 100 105 190	70 100 180 180 320	mV	$I_C = 100 \text{mA}, I_B = 1 \text{mA}$ $I_C = 500 \text{mA}, I_B = 50 \text{mA}$ $I_C = 750 \text{mA}, I_B = 15 \text{mA}$ $I_C = 1A, I_B = 50 \text{mA}$ $I_C = 2A, I_B = 200 \text{mA}$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_	105	200	mΩ	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	1.1	V	I _C = 2A, I _B = 200mA
Base-Emitter Turn On Voltage	V _{BE(on)}	_	_	0.75	V	$V_{CE} = 2V, I_{C} = 100mA$
Output Capacitance	C _{obo}	_	_	20	pF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f⊤	100	250		MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz
Turn-On Time	t _{on}	_	64	_	ns	
Delay Time	t _d	_	20	_	ns	
Rise Time	t _r	_	44	_	ns	V _{CC} = 10V
Turn-Off Time	t _{off}	_	315	_	ns	$I_C = 1A$, $I_{B1} = -I_{B2} = 50mA$
Storage Time	ts	_	275	_	ns	
Fall Time	t _f		40		ns	

Notes: 5. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.

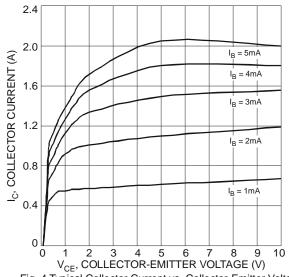
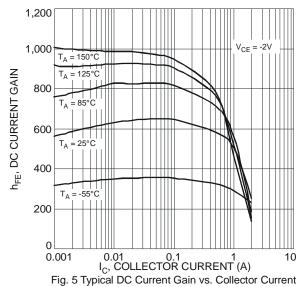
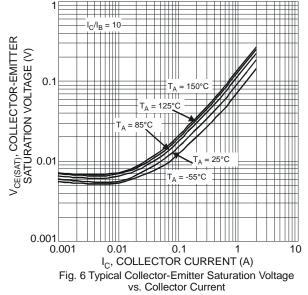
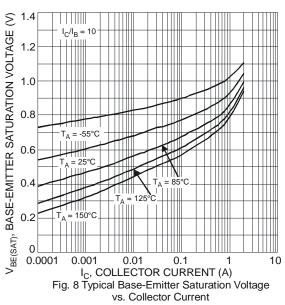


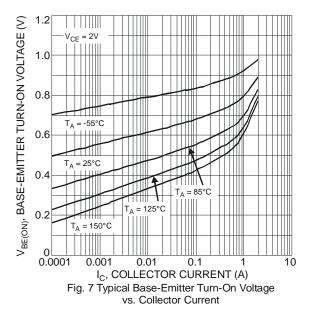
Fig. 4 Typical Collector Current vs. Collector-Emitter Voltage

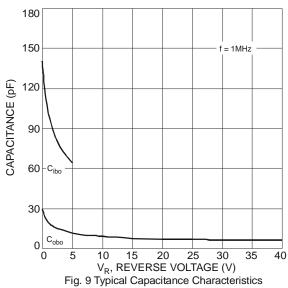




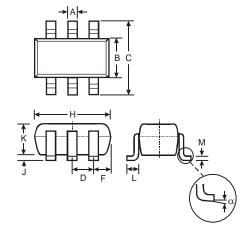








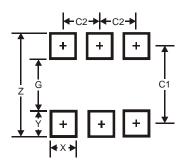
Package Outline Dimensions



SOT363					
Dim	Min	Max			
Α	0.10	0.30			
В	1.15	1.35			
С	2.00	2.20			
D	0.65 Typ				
F	0.40 0.45				
Η	1.80	2.20			
7	0	0.10			
K 0.90 1.0					
L	L 0.25 0.40				
M 0.10 0.22					
α	0°	8°			
All Dimensions in mm					



Suggested Pad Layout



Dimensions	Value (in mm)			
Z	2.5			
G	1.3			
Х	0.42			
Υ	0.6			
C1	1.9			
C2	0.65			

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